

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







MSA-0520

Cascadable Silicon Bipolar MMIC Amplifier



Data Sheet

Description

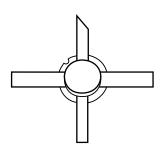
The MSA-0520 is a high performance silicon bipolar Monolithic Microwave Integrated Circuit (MMIC) housed in a hermetic, BeO disk package for good thermal characteristics. This MMIC is designed for use as a general purpose 50Ω gain block. Typical applications include narrow and broad band IF and RF amplifiers in industrial and military applications.

The MSA-series is fabricated using Avago's 10 GHz f_T , 25 GHz f_{MAX} , silicon bipolar MMIC process which uses nitride self-alignment, ion implantation, and gold metallization to achieve excellent performance, uniformity and reliability. The use of an external bias resistor for temperature and current stability also allows bias flexibility.

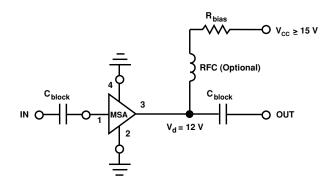
Features

- Cascadable 50 Ω Gain Block
- High Output Power: +23 dBm Typical P_{1 dB} at 1.0 GHz
- Low Distortion:
 33 dBm Typical IP₃ at 1.0 GHz
- 8.5 dB Typical Gain at 1.0 GHz
- Hermetic Metal/Beryllia Microstrip Package

200 mil BeO Package



Typical Biasing Configuration



MSA-0520 Absolute Maximum Ratings

Parameter	Absolute Maximum ^[1]		
Device Current	225 mA		
Power Dissipation ^[2,3]	3.0 W		
RF Input Power	+25 dBm		
Junction Temperature	200°C		
Storage Temperature	−65 to 200°C		

Thermal Resistance^[2,4]:

 $\theta_{ic} = 25$ °C/W

- 1. Permanent damage may occur if any of these limits are exceeded.

- T_{CASE} = 25°C.
 Derate at 40 mW/°C for T_C > 125°C.
 The small spot size of this technique results in a higher, though more accurate determination of θ_{jc} than do alternate methods.

Electrical Specifications^[1], $T_A = 25^{\circ}C$

Symbol	Parameters and Test Conditions: $I_d = 165$ i	Units	Min.	Тур.	Max.		
P _{1 dB}	Output Power at 1 dB Gain Compression	f = 1.0 GHz	dBm	21.0	23.0		
G _P	Power Gain (S ₂₁ ²)	f = 0.1 GHz	dB	7.5	8.5	9.5	
ΔG_P	Gain Flatness	f = 0.1 to 2.0 GHz	dB		±0.75		
f _{3 dB}	3 dB Bandwidth ^[2]		GHz		2.8		
VCMD	Input VSWR	f = 0.1 to 2.0 GHz			2.0:1		
VSWR ——	Output VSWR	f = 0.1 to 2.0 GHz			2.5:1		
IP ₃	Third Order Intercept Point	f = 1.0 GHz	dBm		33.0		
NF _{50 Ω}	50 Ω Noise Figure	f = 1.0 GHz	dB		6.5		
t _D	Group Delay	f = 1.0 GHz	psec		170		
V _d	Device Voltage		V	10.5	12.0	13.5	
dV/dT	Device Voltage Temperature Coefficient		mV/°C		-16.0		

- 1. The recommended operating current range for this device is 80 to 200 mA. Typical performance as a function of current is on the following page.
- 2. Referenced from 0.1 GHz Gain (GP).

MSA-0520 Typical Scattering Parameters ($T_A = 25^{\circ}C$, $I_d = 165$ mA)

Freq.	S-	11		S ₂₁			S ₁₂		S	22	
MHz	Mag	Ang	dB	Mag	Ang	dB	Mag	Ang	Mag	Ang	k
5	.57	-38	14.4	5.25	165	-19.4	.107	38	.67	-35	0.57
25	.25	-90	10.7	3.42	160	-14.9	.180	17	.29	-81	0.93
50	.15	-111	9.5	2.97	163	-14.4	.190	9	.18	-97	1.10
100	.11	-138	8.9	2.80	166	-14.2	.195	3	.11	-113	1.16
200	.10	-152	8.8	2.75	163	-14.1	.197	1	.10	-125	1.17
400	.10	-152	8.7	2.72	152	-14.1	.198	-2	.14	-123	1.16
600	.11	-147	8.6	2.70	140	-14.0	.199	-4	.18	-123	1.14
800	.13	-142	8.5	2.67	128	-14.1	.199	-6	.22	-127	1.12
1000	.15	-140	8.4	2.64	115	-14.1	.198	-8	.27	-131	1.09
1500	.22	-142	8.0	2.52	85	-13.7	.206	-12	.34	-143	0.98
2000	.30	-156	7.4	2.36	55	-13.3	.216	-16	.43	-158	0.85
2500	.37	-170	6.7	2.16	33	-12.9	.227	-18	.48	-166	0.75
3000	.41	170	5.6	1.91	8	-12.7	.232	-23	.51	-177	0.70
3500	.45	149	4.5	1.68	-16	-12.1	.249	-31	.55	173	0.63
4000	.46	124	3.3	1.45	-40	-11.7	.259	-39	.56	162	0.66

Typical Performance, $T_A = 25^{\circ}C$

(unless otherwise noted)

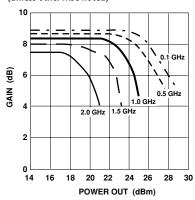


Figure 1. Typical Gain vs. Power Out, $T_A = 25^{\circ}\text{C}$, $I_d = 165 \text{ mA}$.

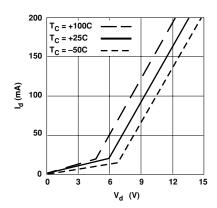


Figure 2. Device Current vs. Voltage.

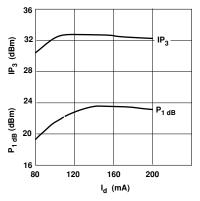


Figure 3. Output Power at 1 dB Gain Compression, Third Order Intercept vs. Current, f = 1.0 GHz.

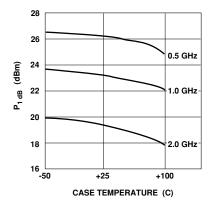


Figure 4. Output Power @ 1 dB Gain Compression vs. Temperature, $I_{\rm d}=$ 165 mA.

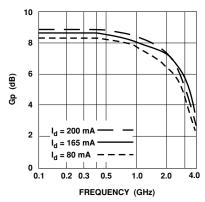


Figure 5. Gain vs. Frequency.

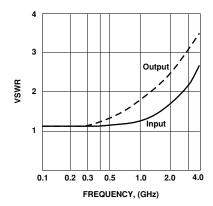
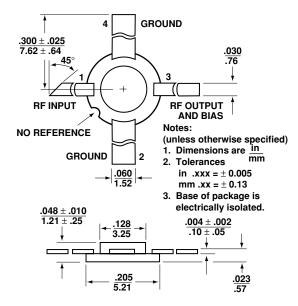


Figure 6. VSWR vs. Frequency, $I_d=165\ mA$.

Ordering Information

Part Numbers	No. of Devices	Comments
MSA-0520	100	Bulk

200 mil BeO Package Dimensions



For product information and a complete list of distributors, please go to our web site: www.avagotech.com

